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Data sheet acquired from Harris Semiconductor

CD4011B, CD4012B, CD4023B Types

CMOS NAND GATES

High-Voltage Types (20-Volt Rating)

Quad 2 Input - CD4011B Dual 4 Input - CD4012B Triple 3 Input - CD4023B

■ CD4011B, CD4012B, and CD4023B NAND gates provide the system designer with direct implementation of the NAND function and supplement the existing family of CMOS gates. All inputs and outputs are buffered.

The CD4011B, CD4012B, and CD4023B types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

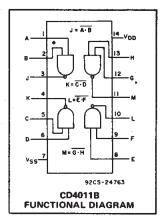
- Propagation delay time = 60 ns (typ.) at C_L = 50 pF, V_{DD} = 10 V
- Buffered inputs and outputs
- Standardized symmetrical output characteristics
- Maximum input current of 1 μA at 18 V over full package temperature range; 100 nA at 18 V and 25°C
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Noise margin (over full package temperature range:

1 V at V_{DD} = 5 V

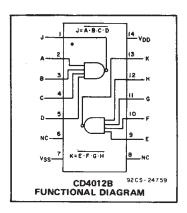
2 V at V_{DD} = 10 V

2.5 V at V_{DD} = 15 V

 Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of "B" Series CMOS Devices"



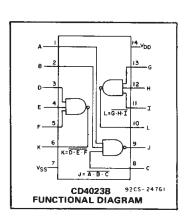
MAXIMUM RATINGS, Absolute-Maximum Values:	
DC SUPPLY-VOLTAGE RANGE, (VDD)	
Voltages referenced to VSS Terminal)0.5V to +20V	
INPUT VOLTAGE RANGE, ALL INPUTS0.5V to VDD +0.5V	
DC INPUT CURRENT, ANY ONE INPUT ±10mA	
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -55°C to +100°C	
For T _A = +100°C to +125°C Derate Linearity at 12mW/°C to 200mW	
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR TA = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	
OPERATING-TEMPERATURE RANGE (T _A)55°C to +125°C	
STORAGE TEMPERATURE RANGE (T _{stg})65°C to +150°C	
LEAD TEMPERATURE (DURING SOLDERING):	



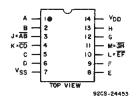
RECOMMENDED OPERATING CONDITIONS

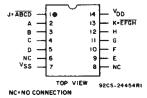
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

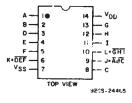
CHARACTERISTIC	LIM	LIBUTO	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range)	. 3	18	V



TERMINAL ASSIGNMENTS







CD4011B

CD4012B

CD4023B

CD4011B, CD4012B, CD4023B Types

STATIC ELECTRICAL CHARACTERISTICS

CHARACTER-	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)						UNITS	
ISTIC	٧o	VIN	VDD					+25			JUNITS
	(V)	(V)	(V)	-55	-40	+85	+125	Min.	Тур.	Max.	
Quiescent Device Current, IDD Max.	-	0,5	5	0.25	0.25	7.5	7.5		0.01	0.25	
	-	0,10	10	0.5	0.5	15	15	-	0.01	0.5	۵.,۵
	_	0,15	15	1	1	30	30	_	0.01	1	μΑ
	-	0,20	20	5	5	150	150	- 1	0.02	5	
Output Low	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1		
(Sink) Current	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	_	
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	_	
Output High	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	mA
(Source) Current,	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	
IOH Min.	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8		
Output Voltage:	-	0,5	5		0	.05		-	0	0.05	
Low-Level,	_	0,10	10	0.05			_	0	0.05		
VOL Max.		0,15	15	0.05			=	0	0.05	v	
Output Voltage:		0,5	5	4.95			4.95	5	-	·	
High-Level,	-	0,10	10	9.95			9.95	10	_		
VOH Min.	-	0,15	15		14.95			14.95	15	-	
Input Low	4.5	-	5			1.5		-	_	1.5	
Voltage, VIL Max.	9	-	10			3	****	-		3]
	13.5	_	15	4			-		4	V	
Input High Voltage, VIH Min.	0.5,4.5	-	5	3.5			3.5	_] "	
	1,9		10	7			7				
	1.5,13.5	_	15	11 11							
Input Current IIN Max.		0,18	18	±0.1	±0.1	±1	±1		±10 ⁻⁵	±0.1	μА

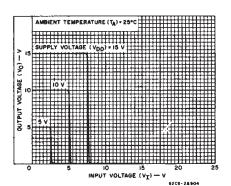


Fig. 1 — Typical voltage transfer characteristics.

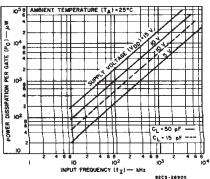


Fig.2 - Typical power dissipation characteristics.

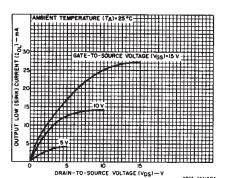


Fig.3 — Typical output low (sink) current characteristics.

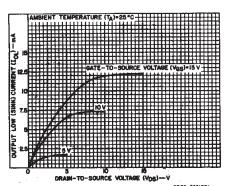


Fig. 4 — Minimum output low (sink) current characteristics.

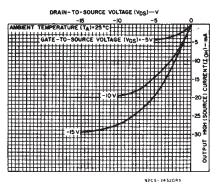


Fig.5 - Typical output high (source) current characteristics.

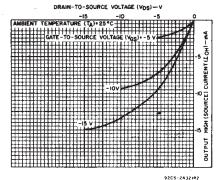


Fig.6 — Minimum output high (source) current characteristics.

CD4011B, CD4012B, CD4023B Types

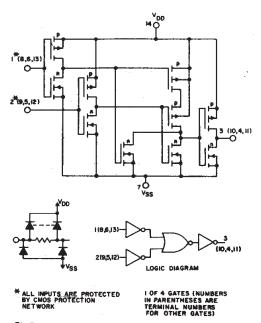


Fig.7 - Schematic and logic diagrams for CD4011B.

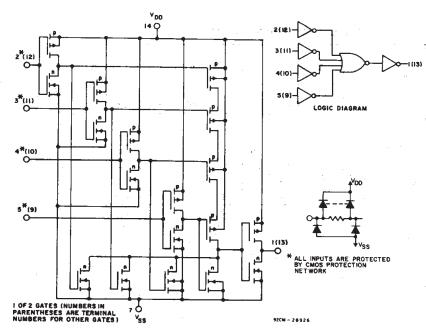


Fig.8 — Schematic and logic diagrams for CD4012B.

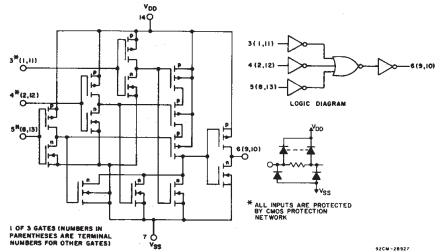


Fig. 9 - Schematic and logic diagrams for CD4023B.

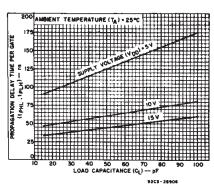


Fig. 10 - Typical propagation delay time per gate as a function of load capacitance,

DYNAMIC ELECTRICAL CHARACTERISTICS

At $T_A = 25^{\circ}C$; Input t_r , $t_f = 20$ ns, $C_L = 50$ pF, $R_L = 200$ k Ω

CHARACTERISTIC	TEST CONDITIONS		LIN		
		V _{DD}	TYP.	MAX.	UNITS
Propagation Delay Time, tphL, tpLH		5	125	250	
		10	60	120	ns
		15	45	90	
Transition Time,		5	100	200	
		10	50	100	ns
		15	40	80	
Input Capacitance, CIN	Any Input		5	7.5	pF

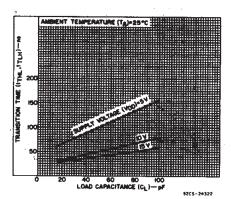


Fig. 11 - Typical transition time as a function of load capacitance.

CD4011B, CD4012B, CD4023B Types

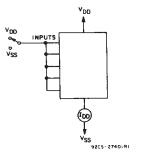


Fig. 12 - Quiescent-device-current test circuit.

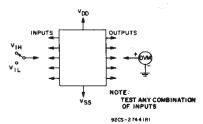


Fig. 13 - Input-voltage test circuit.

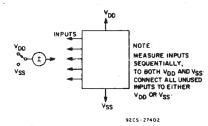
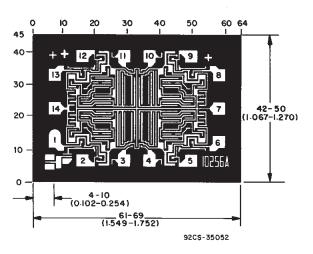
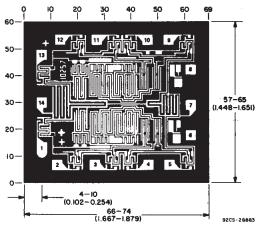


Fig. 14 - Input-current test circuit.

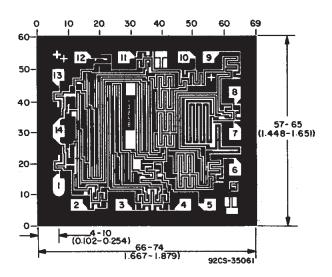
Chip Dimensions and Pad Layouts



CD4011BH



CD4012BH



CD4023BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

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